

ABSTRACT OF THE DISCLOSURE

A chemical-mechanical polishing (CMP) proximity correction method for polishing a wafer is provided. The wafer has a polish area and a protected area. The
5 method includes forming a material layer over the wafer to cover the polish area and the protected area and then forming a protective layer over the material layer. Thereafter, the protective layer is patterned so that the remaining protective layer is at a distance away from the boundary of the polish area to reduce shadowing effects. Because the boundary of the protective layer above the material layer recedes to an area at a distance
10 away from polish area, the whole polish area can be cleanly polished.